



PSMN6R4-30MLD

N-channel 30 V, 6.4 mΩ logic level MOSFET in LFAK33 using NextPowerS3 Technology

21 January 2019

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in an LFAK33 package. The NextPowerS3 portfolio, utilising Nexperia's unique "SchottkyPlus" technology, delivers high efficiency and the low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like body diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G , Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

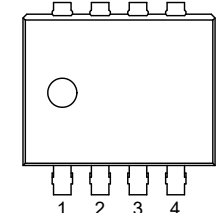
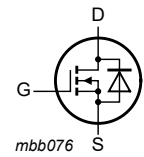
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	-	66	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	51	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	6.9	8.3	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	1.8	3	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK33 (SOT1210)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R4-30MLD	LFAK33	Plastic single ended surface mounted package (LFAK33); 8 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN6R4-30MLD	6D430L

8. Limiting values

Table 5. Limiting values

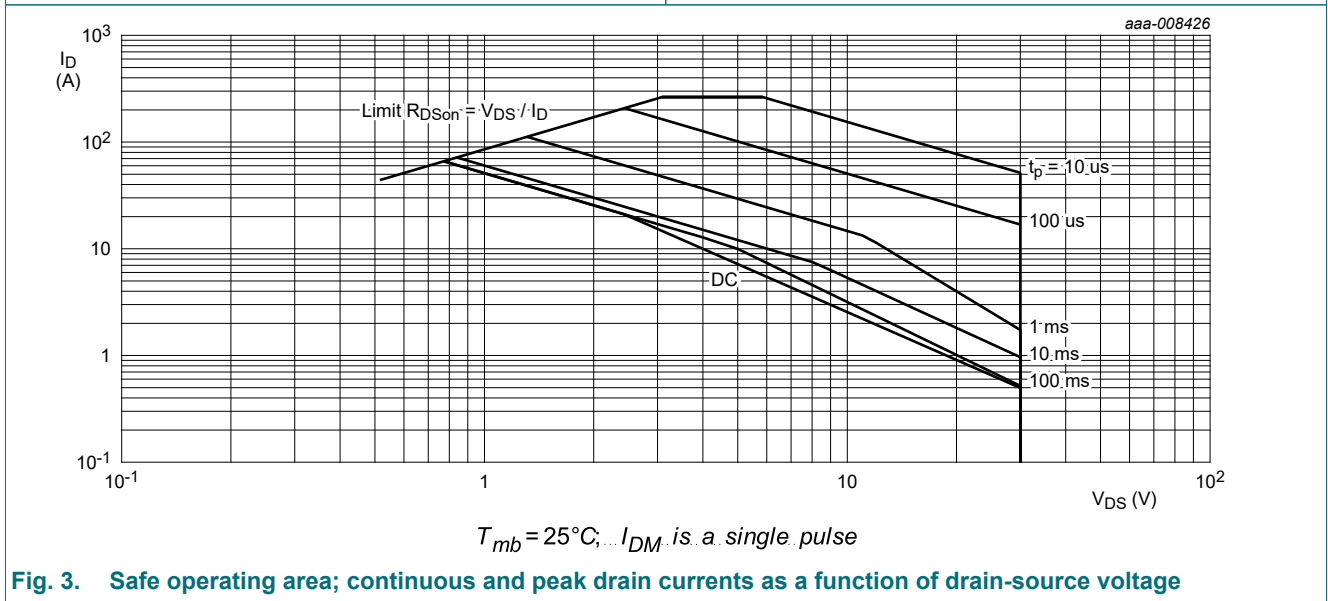
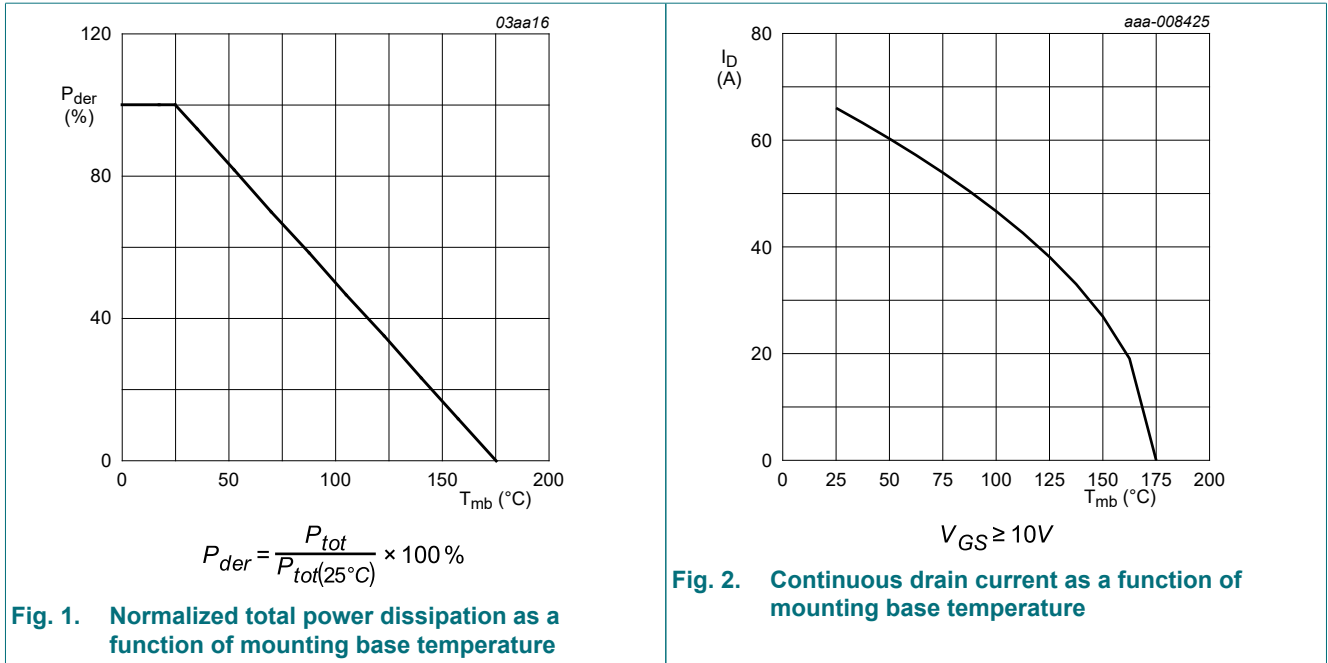
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	51	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	66	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 2	-	47	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3	-	264	A
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	43	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	264	A
Avalanche ruggedness					

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Symbol	Parameter	Conditions		Min	Max	Unit
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 15\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped; $t_p = 159\ \mu\text{s}$	[1]	-	46.6	mJ

[1] Protected by 100% test



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	2.72	2.94	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	57	-	K/W
		Fig. 6	-	178	-	K/W

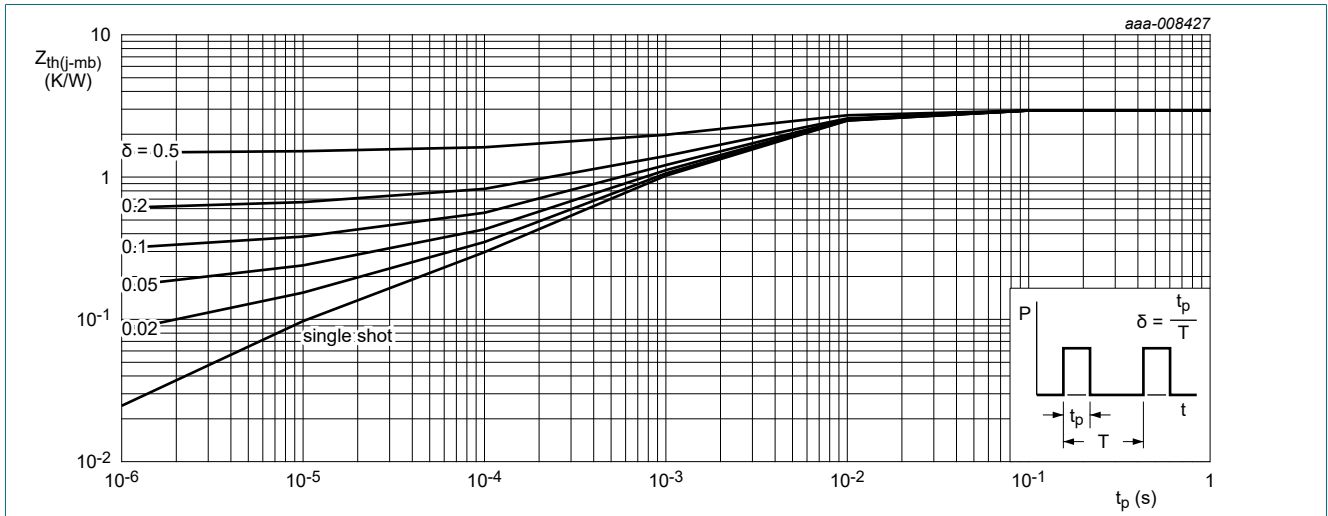


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.7	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-3.8	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	0.45	-	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = -16\text{ V}$; $V_{DS} = 0\text{ V}$; $T_j = 25\text{ °C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	6.9	8.3	mΩ
		$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 150\text{ °C}$; Fig. 10 ; Fig. 11	-	-	13.7	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	5.3	6.3	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 150\text{ °C}$; Fig. 10 ; Fig. 11	-	-	10.4	mΩ
R_G	gate resistance	$f = 1\text{ MHz}$	-	2.36	5.8	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 12 ; Fig. 13	-	13.7	19	nC
		$I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	6.5	9	nC
		$I_D = 0\text{ A}$; $V_{DS} = 0\text{ V}$; $V_{GS} = 10\text{ V}$	-	12.2	-	nC
Q_{GS}	gate-source charge	$I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	1.7	4	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.5	-	nC
Q_{GD}	gate-drain charge		-	1.8	3	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 15\text{ A}$; $V_{DS} = 15\text{ V}$; Fig. 12 ; Fig. 13	-	2.2	-	V
C_{iss}	input capacitance	$V_{DS} = 15\text{ V}$; $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$; Fig. 14	-	832	-	pF
C_{oss}	output capacitance		-	587	-	pF
C_{rss}	reverse transfer capacitance		-	64	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}$; $R_L = 1\text{ Ω}$; $V_{GS} = 4.5\text{ V}$; $R_{G(ext)} = 5\text{ Ω}$	-	9	-	ns
t_r	rise time		-	16.2	-	ns
$t_{d(off)}$	turn-off delay time		-	10.5	-	ns
t_f	fall time		-	10.9	-	ns
Q_{oss}	output charge	$V_{GS} = 0\text{ V}$; $V_{DS} = 15\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$	-	12.6	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 10\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; Fig. 15	-	0.8	1.2	V
t_{rr}	reverse recovery time	$I_S = 15\text{ A}$; $dI_S/dt = -100\text{ A/μs}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 15\text{ V}$; Fig. 16	-	23.4	-	ns
Q_r	recovered charge		[1]	12.6	-	nC
t_a	reverse recovery rise time		-	10.6	-	ns
t_b	reverse recovery fall time		-	12.8	-	ns
S	softness factor		-	1.2	-	

[1] includes capacitive recovery

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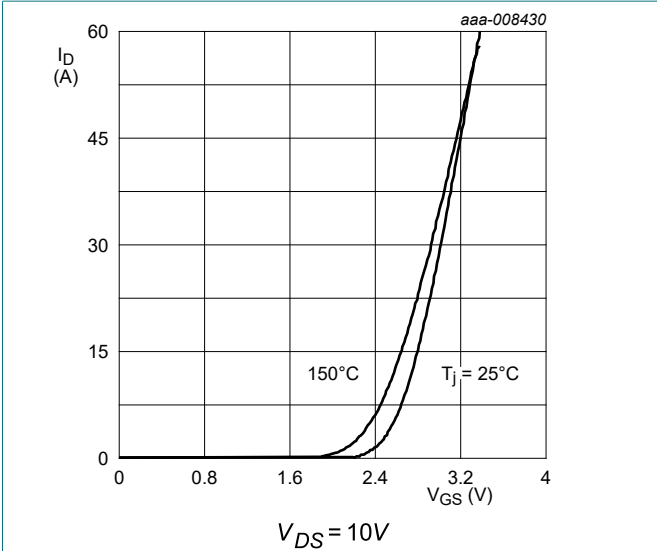


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

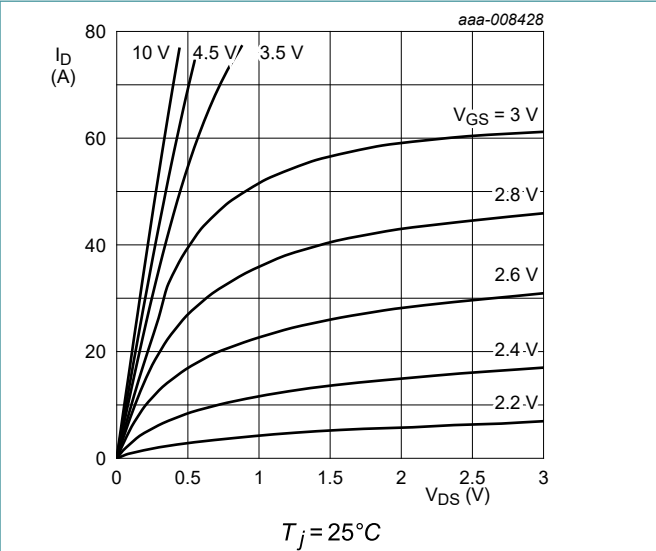


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

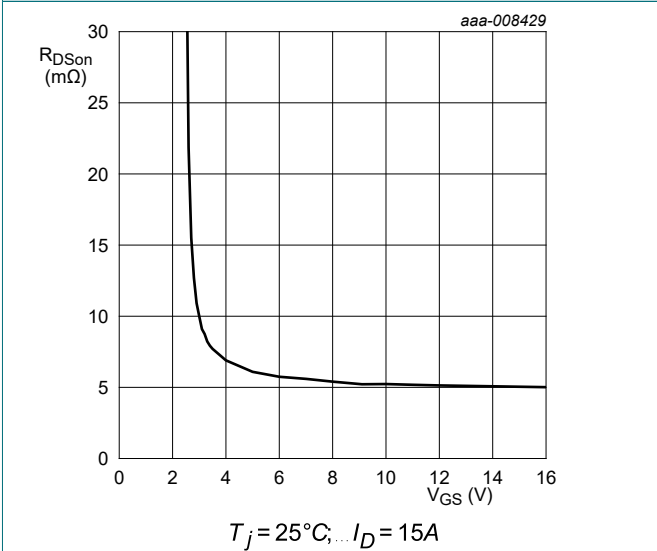


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

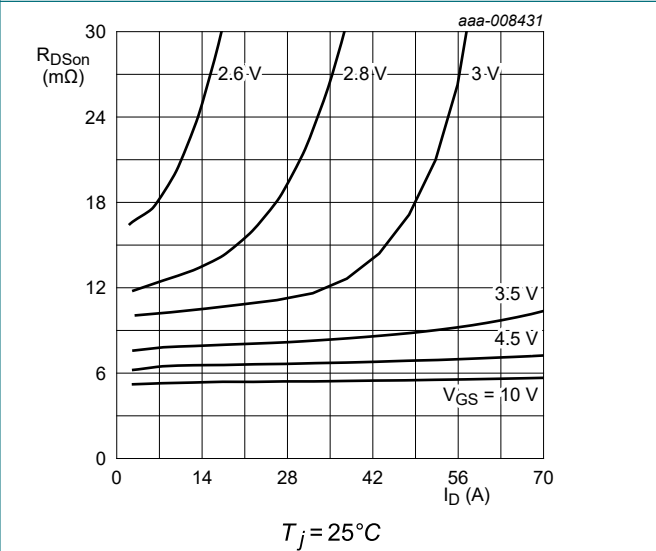
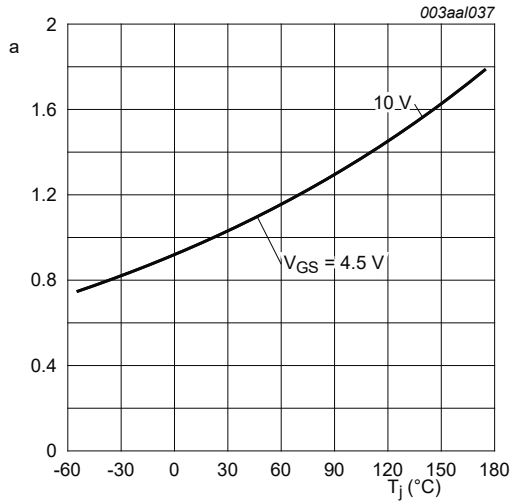


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

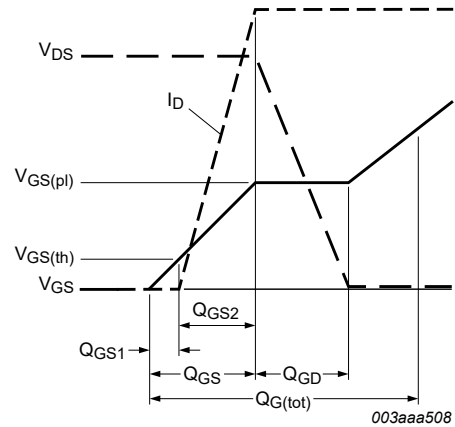
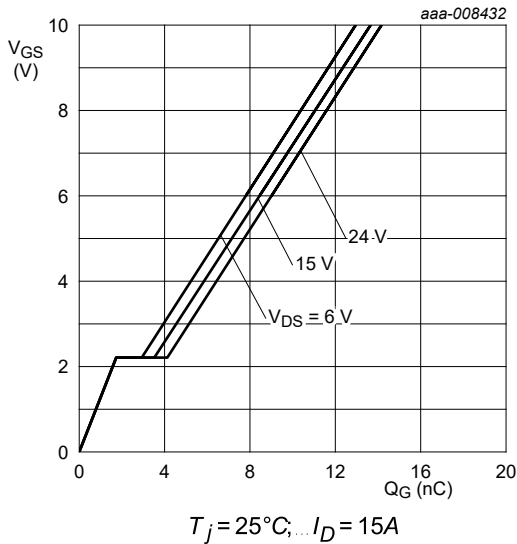
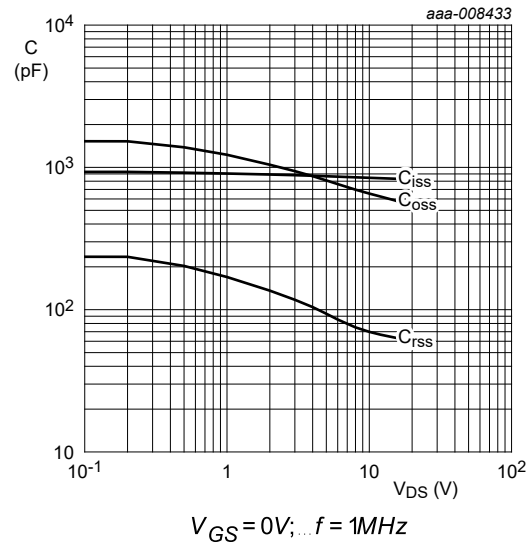


Fig. 12. Gate charge waveform definitions



$T_j = 25^{\circ}\text{C}; \dots I_D = 15\text{A}$

Fig. 13. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; \dots f = 1\text{MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

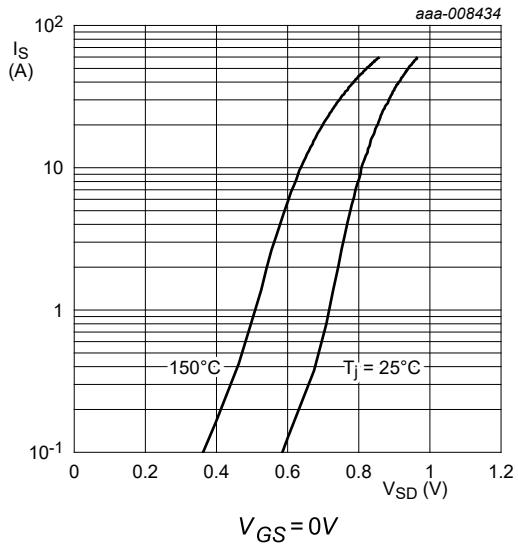


Fig. 15. Source current as a function of source-drain voltage; typical values

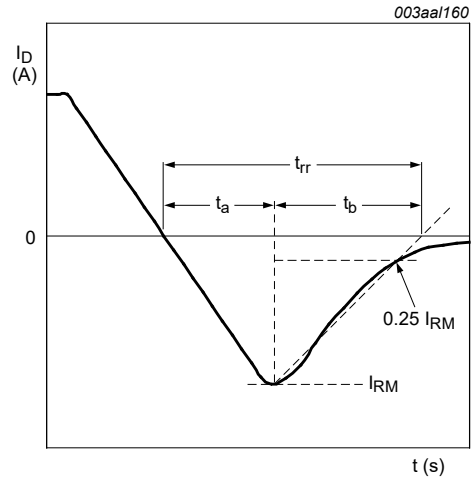


Fig. 16. Reverse recovery timing definition

11. Package outline

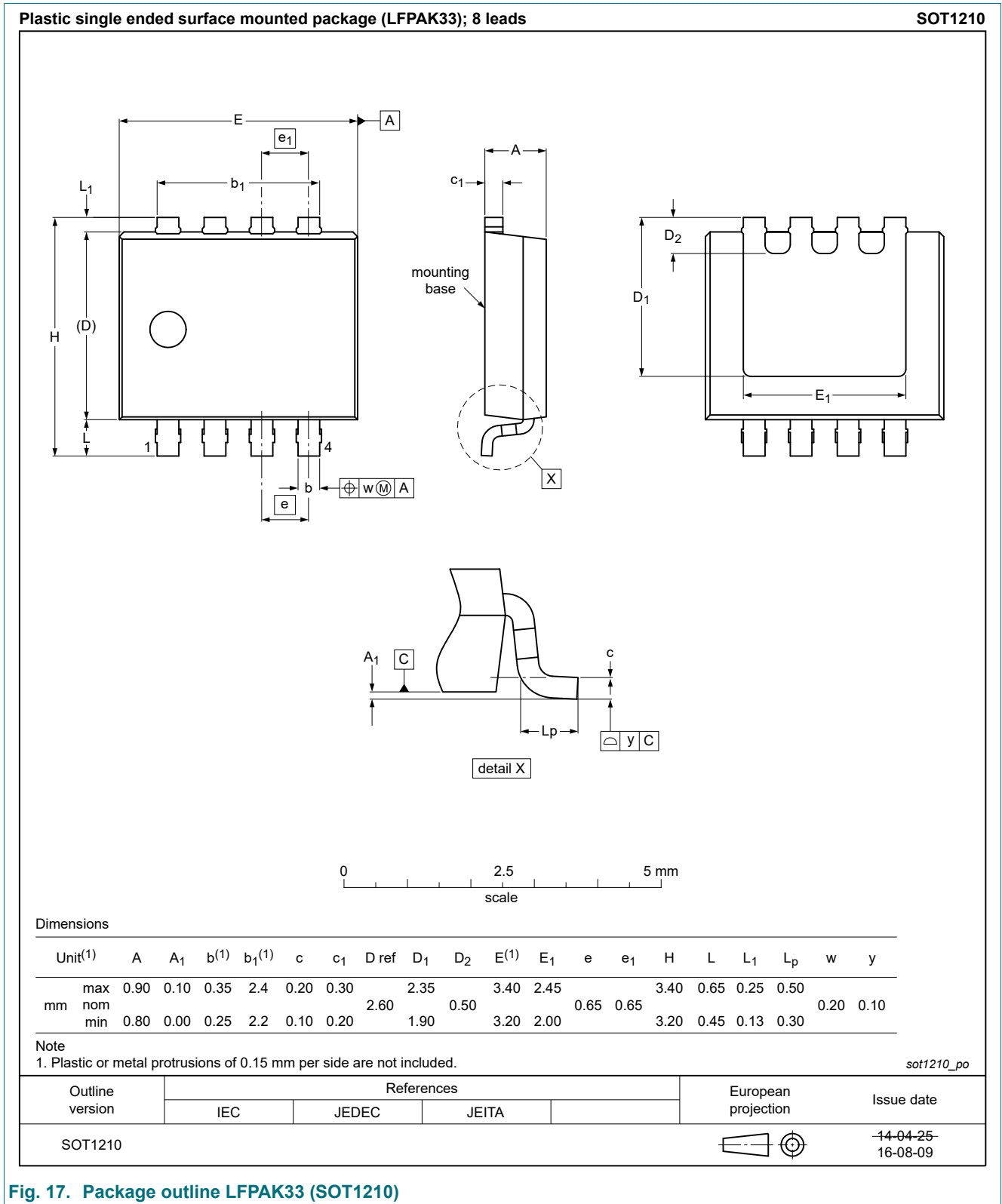


Fig. 17. Package outline LPAK33 (SOT1210)

12. Soldering

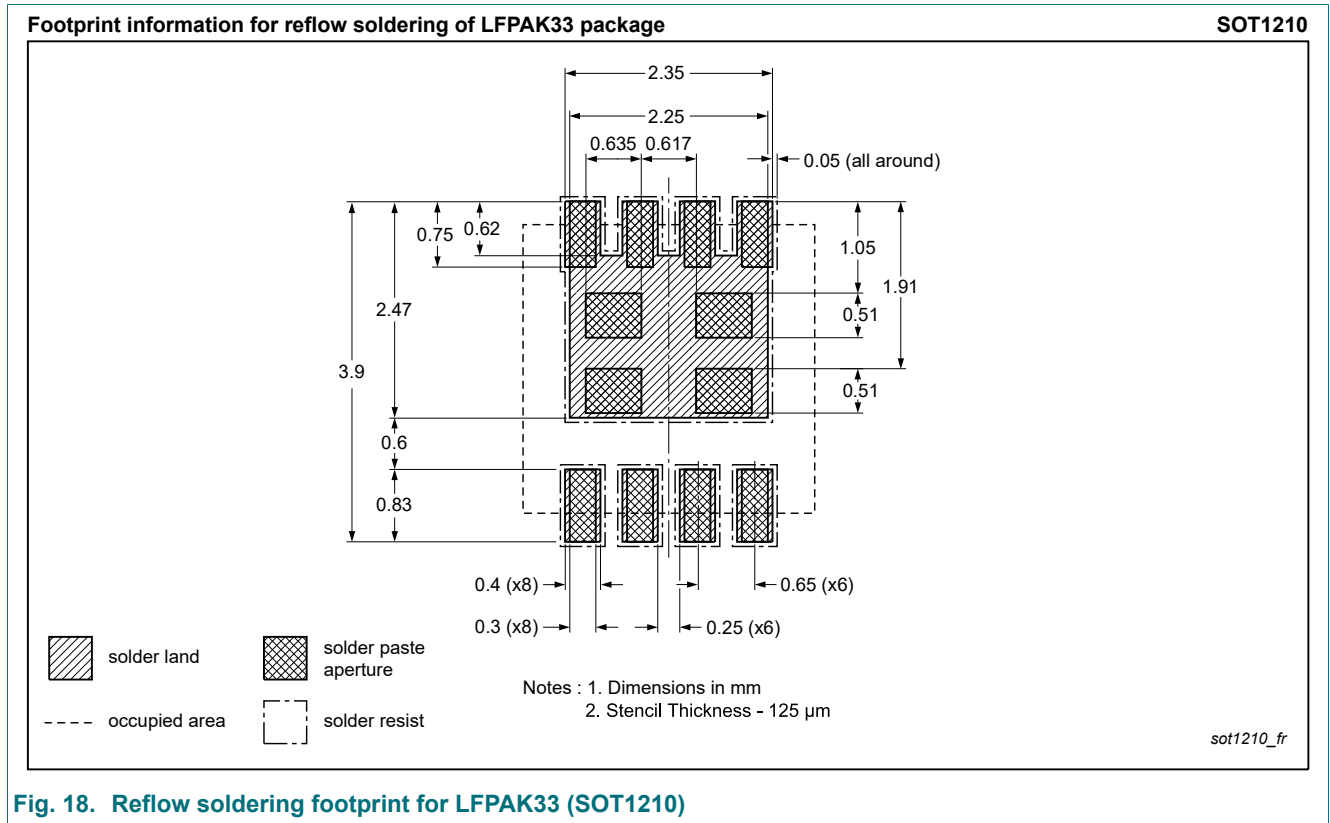


Fig. 18. Reflow soldering footprint for LFPAK33 (SOT1210)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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